

**FR151
THRU
FR157**

Features

- Low Cost
- Low Leakage
- Low Forward Voltage Drop
- High Current Capability
- Fast Switching Speed For High Efficiency

**1.5 Amp
Silicon Rectifier
50 to 1000 Volts**

Maximum Ratings

- Operating Temperature: -65°C to +175°C
- Storage Temperature: -65°C to +175°C

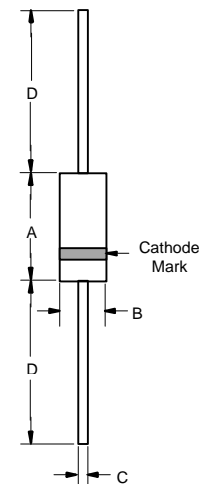
Microsemi Catalog Number	Device Marking	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
FR151	---	50V	35V	50V
FR152	---	100V	70V	100V
FR153	---	200V	40V	200V
FR154	---	400V	280V	400V
FR155	---	600V	420V	600V
FR156	---	800V	560V	800V
FR157	---	1000V	700V	1000V

Electrical Characteristics @ 25°C Unless Otherwise Specified

Average Forward Current	$I_{F(AV)}$	1.5 A	$T_A = 55^\circ\text{C}$
Peak Forward Surge Current	I_{FSM}	60A	8.3ms, half sine
Maximum Instantaneous Forward Voltage	V_F	1.3V	$I_{FM} = 1.5\text{A}; T_A = 25^\circ\text{C}$
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	5.0 μA 100 μA	$T_A = 25^\circ\text{C}$ $T_A = 100^\circ\text{C}$
Maximum Reverse Recovery Time FR151-154 FR155 FR156-157	T_{rr}	150ns 250ns 500ns	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$
Typical Junction Capacitance	C_J	20pF	Measured at 1.0MHz, $V_R=4.0\text{V}$

*Pulse Test: Pulse Width 300 μsec , Duty Cycle 1%

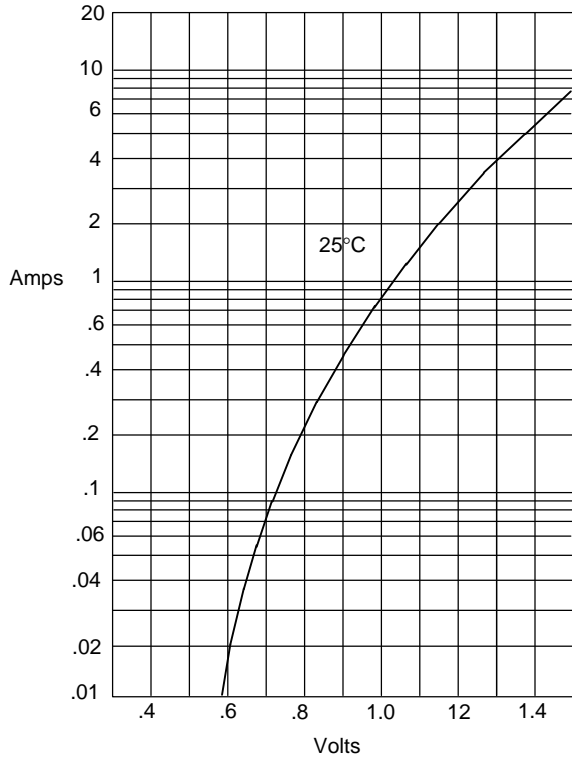
DO-15



DIM	DIMENSIONS				NOTE
	INCHES		MM		
A	.230	.300	5.80	7.60	
B	.104	.140	2.60	3.60	
C	.026	.034	.70	.90	
D	1.000	---	25.40	---	

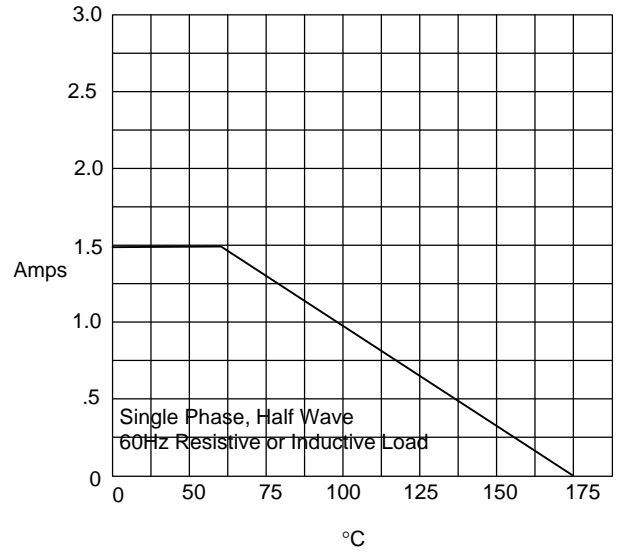
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Figure 1
Typical Forward Characteristics



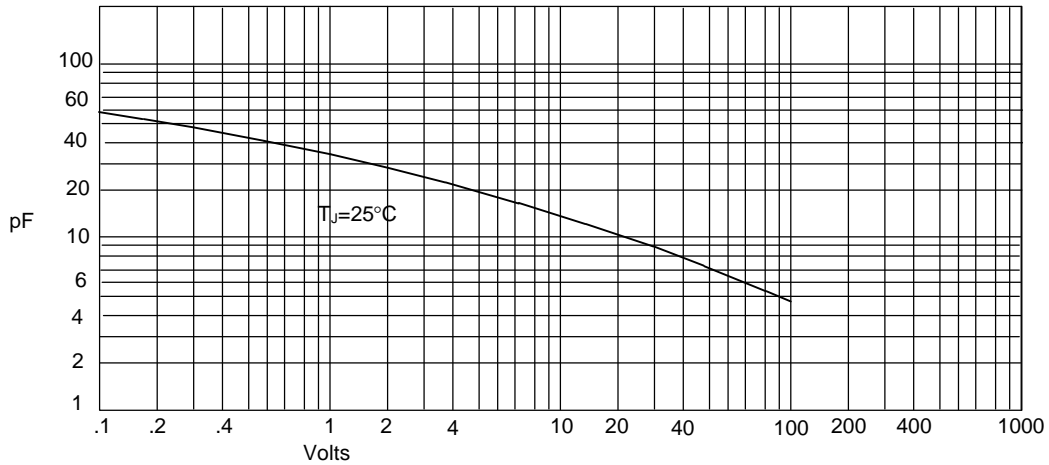
Instantaneous Forward Current - Amperes *versus*
Instantaneous Forward Voltage - Volts

Figure 2
Forward Derating Curve



Average Forward Rectified Current - Amperes *versus*
Ambient Temperature - °C

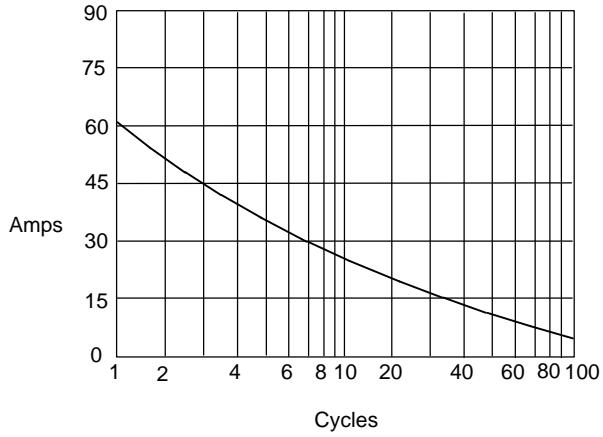
Figure 3
Junction Capacitance



Junction Capacitance - pF *versus*
Reverse Voltage - Volts

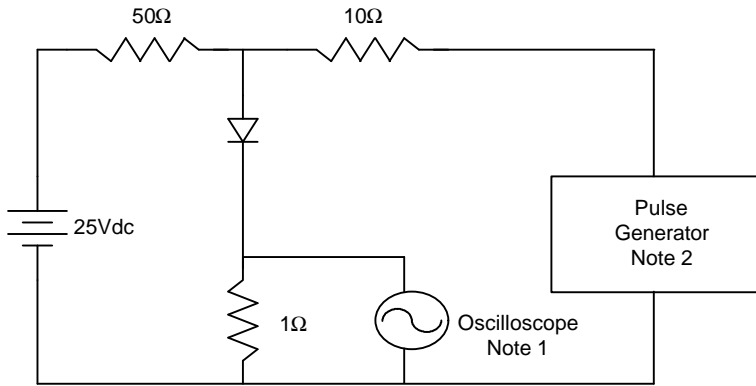
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Figure 4
Maximum Non-Repetitive Forward Surge Current



Peak Forward Surge Current - Amperes versus
Number Of Cycles At 60Hz - Cycles

Figure 5
Reverse Recovery Time Characteristic And Test Circuit Diagram



Notes:

1. Rise Time = 7ns max.
Input impedance = 1 megohm, 22pF
2. Rise Time = 10ns max.
Source impedance = 50 ohms
3. Resistors are non-inductive

